

INTERSIL

2N3823

N-Channel JFET

FOR VHF AMPLIFIER OSCILLATOR MIXER APPLICATIONS

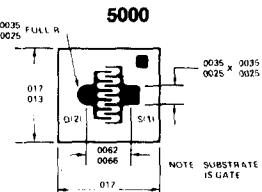
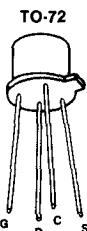
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- Noise Figure < 2.5 dB at 100 MHz
- Low Capacitance
- Transconductance up to 6500 μmho

ABSOLUTE MAXIMUM RATINGS (25°C)

Gate-Source Voltage	-30V
Gate-Drain Voltage	-30V
Gate Current	10 mA
Total Device Dissipation at (or below) 25°C		
Free-Air Temperature	300 mW
Storage Temperature Range	-65 to +200°C
Lead Temperature 1/16" From Case to 10 Sec	300°C

PIN CONFIGURATION CHIP TOPOGRAPHY



ORDERING INFORMATION

TO-72	WAFER	DICE
2N3823	2N3823/W	2N3823/D

ELECTRICAL CHARACTERISTICS (25°C)

CHARACTERISTIC	MIN	MAX	UNIT	TEST CONDITIONS
Igss Gate Reverse Current	-0.5	nA		VGS = -20V, VDS = 0
	-0.5	μA		150°C
BVGSS Gate-Source Breakdown Voltage	-30			IG = 1 μA , VDS = 0
VGS(off) Gate-Source Cutoff Voltage	-8		V	VDS = 15V, ID = 0.5 nA
Vgs Gate-Source Voltage	-1.0	-7.5		VDS = 15V, ID = 400 μA
Isoss Saturation Drain Current	4	20	mA	VDS = 15V, VGS = 0 (Note 3)
gfs Common-Source Forward Transconductance	3,500	6,500		f = 1 kHz (Note 1)
Vfs Common-Source Forward Transadmittance	3,200			f = 100 MHz
gos Common-Source Output Transconductance		35	μmho	f = 1 kHz (Note 1)
giss Common-Source Input Conductance		800		VDS = 15V, VGS = 0
goss Common-Source Output Conductance		200		f = 200 MHz
Ciss Common-Source Input Capacitance		6	pF	
Crss Common-Source Reverse Transfer Capacitance		2		f = 1 MHz
NF Noise Figure		2.5	dB	VDS = 15V, VGS = 0 RG = 1 k Ω
				f = 100 MHz

NOTE 1: These parameters are measured during a 2 msec interval 100 msec after d-c power is applied.